

AMENDMENTS TO THE SPECIFICATION

Please amend the paragraphs beginning at page 26, line 10, as follows:

FIG. 28 is a sectional view showing another example of a thin film field effect transistor of the related art; and

FIG. 29A and 29B are sectional views showing static induction transistors of the related art; and

FIG. 30 is another sectional view of a configuration of an active device 40 according to a fourth embodiment of the present invention.

Please amend the paragraph beginning at page 52, line 17, as follows:

It is explained in the above description that the high resistance layer 7 is disposed between the source electrode 3 and the organic semiconductor layer 5 as illustrated. But the present invention is not limited to this. The high resistance layer 7 may also be disposed between the source electrode 3 and the organic semiconductor layer 5, and/or between the drain electrode 4 and the organic semiconductor layer 5, and/or between the low resistance layer 6 and the organic semiconductor layer 5 as shown in FIG. 30. The above configurations have the same effects as that described above.